

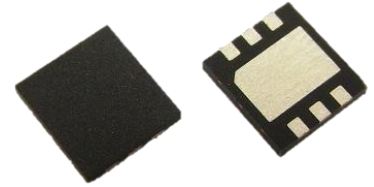
FEATURES

- High Voltage Operation : VDS=50V
- High Power : 42.5dBm (typ.) @ Psat
- High Efficiency : 60% (typ.) @ Psat
- Power Gain : 19.5dB (typ.) @ f=2.65GHz
- Proven Reliability

DESCRIPTION

Sumitomo's GaN-HEMT offers high efficiency, ease of matching, greater consistency and broad bandwidth for high power amplifiers with 50V operation, and gives you higher gain.

This new product is ideally suited for use up to 3.8GHz W-CDMA & LTE design requirements as it offers high gain, long term reliability and ease of use. This device target applications are driver stage and final stage of micro cell base transceiver stations.



ABSOLUTE MAXIMUM RATINGS

Item	Symbol	Condition	Rating	Unit
Operating Voltage	VDS		55	V
Drain-Source Voltage	VDS *	VGS=-8V	160	V
Gate-Source Voltage	VGS *		-15	V
Total Power Dissipation	Pt *		14.8	W
Storage Temperature	Tstg		-40 to +125	deg.C
Channel Temperature	Tch		250	deg.C

* : Case Temperature Tc=25deg.C

RECOMMENDED OPERATING CONDITION

Item	Symbol	Condition	Limit	Unit
DC Input Voltage	VDS		≤ 55	V
Forward Gate Current	IGF	RG=15ohm	≤ 33	mA
Reverse Gate Current	IGR	RG=15ohm	≥ -0.5	mA
Channel Temperature	Tch		≤ 200	deg.C
Average Output Power	Pave.		≤ 39.5	dBm

ELECTRICAL CHARACTERISTICS (Case Temperature Tc=25deg.C)

Item	Symbol	Condition	Limit			Unit
			Min.	Typ.	Max.	
Pinch-Off Voltage	Vp	VDS=50V, IDS=3.9mA	-1.0	-1.5	-2.0	V
Saturated Power	Psat *1	VDS=50V, IDS(DC)≈0mA f=2.65GHz	41.5	42.5	-	dBm
Drain Efficiency	DE *2	VDS=50V	11.5	13.5	-	%
Power Gain	Gp *2	IDS(DC)≈75mA f=2.65GHz	18.5	19.5	-	dB
Thermal Resistance	Rth *3	Channel to Case at 13.5W PDC	-	9.0	10.5	deg.C/W

Note: *1 : 10%-duty RF pulse (DC supply constant)

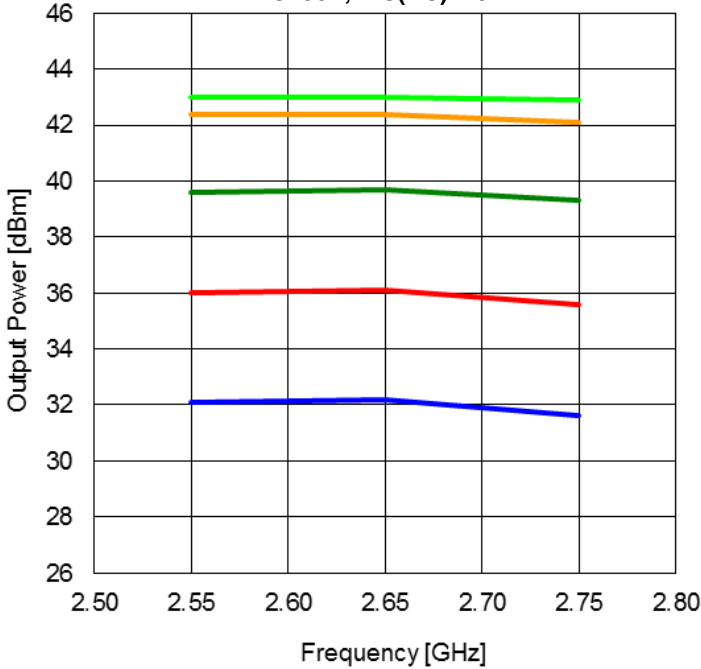
*2 : Pout=29.0dBm, CW modulation Signal (W-CDMA)

*3 : Sampling Test : samples size 10pcs. Criteria(accept / reject)=(0 / 1)

RoHS COMPLIANCE Yes

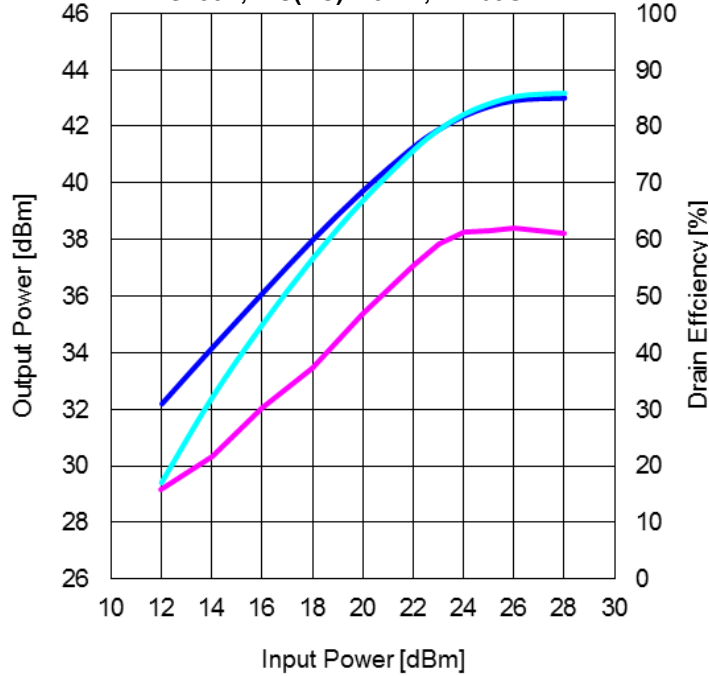
RF characteristics @f=2.65GHz fine tuned

Output Power vs. Frequency
VDS=50V, IDS(DC)=75mA



Pin=12dBm Pin=16dBm Pin=20dBm
Pin=24dBm Pin=28dBm

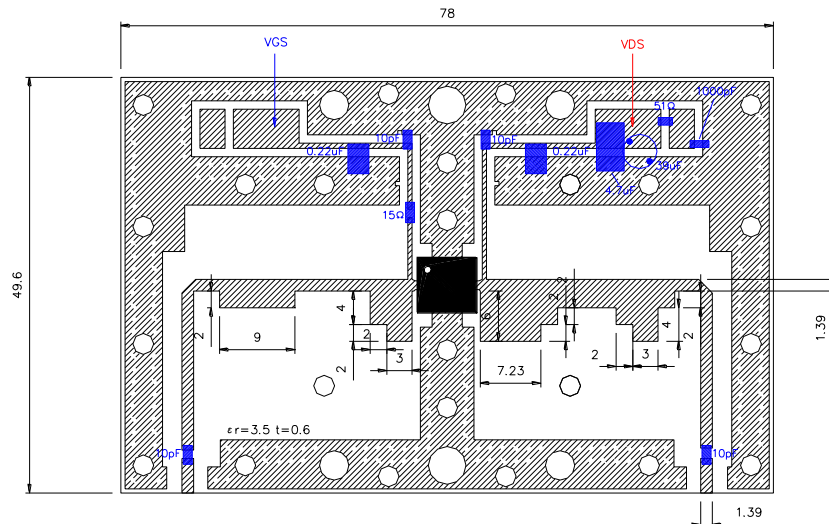
Output Power and Drain Efficiency vs. Input Power
VDS=50V, IDS(DC)=75mA, f=2.65GHz



Pout (class AB) Pout (class B) DE (class B)

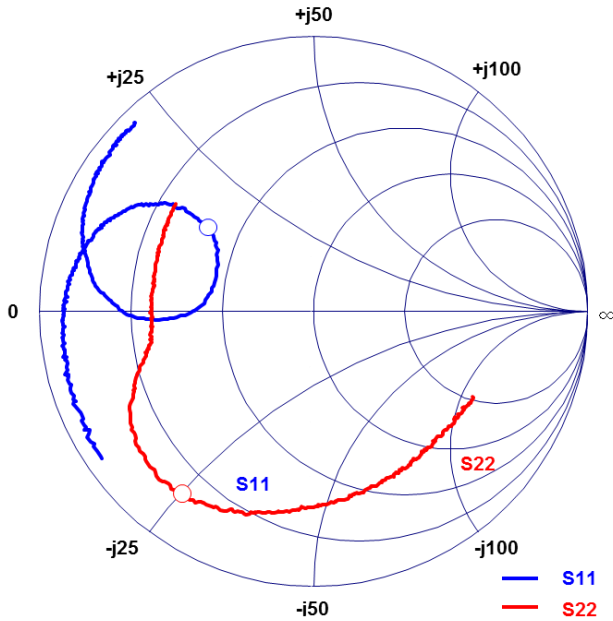
Test Fixture

Pulse Signal (10%-duty, DC : constant)

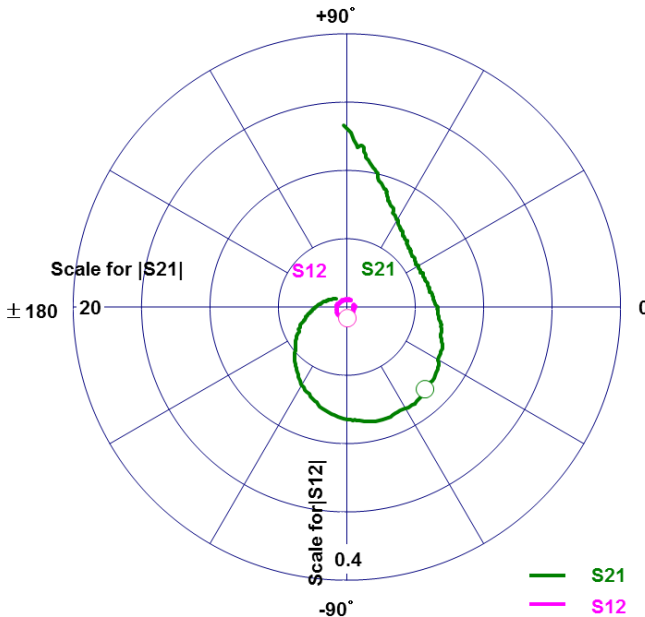


S-Parameters @VDS=50V, IDS(DC)=75mA, f=0.5 to 4.5GHz
 ZI = Zs = 50ohm Marker : 2.65GHz

- Reference DATA -



Freq. GHz	S11			S21		S12		S22	
	MAG	ANG		MAG	ANG	MAG	ANG	MAG	ANG
0.5	0.94	-145.31	13.30	91.01	0.011	21.37	0.66	-28.08	
0.6	0.93	-153.18	11.44	83.73	0.010	8.31	0.65	-32.34	
0.7	0.93	-159.35	10.13	77.68	0.010	9.17	0.65	-36.21	
0.8	0.93	-164.39	9.08	71.83	0.011	-4.58	0.65	-39.99	
0.9	0.92	-169.16	8.33	68.42	0.011	-3.00	0.65	-43.45	
1.0	0.92	-172.84	7.66	63.36	0.011	-10.12	0.65	-47.12	
1.1	0.92	-176.10	7.23	58.50	0.010	-7.94	0.65	-51.79	
1.2	0.91	-179.35	6.88	53.27	0.011	-12.49	0.65	-56.31	
1.3	0.91	-177.97	6.56	48.81	0.010	-16.31	0.65	-60.53	
1.4	0.90	-175.00	6.31	44.14	0.011	-17.10	0.66	-64.28	
1.5	0.90	-172.49	6.12	40.04	0.011	-22.54	0.67	-68.59	
1.6	0.89	-169.84	6.06	35.18	0.011	-18.48	0.68	-73.06	
1.7	0.88	-167.12	6.04	29.57	0.011	-19.39	0.68	-77.30	
1.8	0.87	-164.14	6.06	24.31	0.011	-29.48	0.69	-82.07	
1.9	0.85	-161.11	6.04	18.86	0.011	-35.17	0.70	-86.12	
2.0	0.84	-158.02	6.18	13.24	0.010	-35.23	0.71	-90.67	
2.1	0.81	-155.09	6.34	7.29	0.012	-43.30	0.72	-94.41	
2.2	0.78	-151.69	6.63	-0.03	0.012	-44.92	0.74	-99.91	
2.3	0.74	-148.34	6.88	-8.37	0.013	-51.81	0.76	-104.93	
2.4	0.69	-145.56	7.19	-17.15	0.014	-57.91	0.78	-110.13	
2.5	0.62	-142.80	7.64	-26.57	0.015	-67.64	0.79	-116.17	
2.6	0.54	-141.48	8.19	-37.72	0.016	-76.81	0.82	-121.78	
2.7	0.44	-144.34	8.53	-52.24	0.017	-93.41	0.82	-129.78	
2.8	0.38	-158.22	8.65	-68.15	0.017	-109.06	0.82	-137.41	
2.9	0.40	-175.80	8.30	-85.98	0.017	-129.04	0.79	-145.57	
3.0	0.51	-177.24	7.67	-103.25	0.017	-143.47	0.75	-152.85	
3.1	0.64	-177.66	6.80	-116.73	0.016	-164.91	0.71	-157.85	
3.2	0.72	-178.16	5.81	-129.54	0.014	-173.61	0.66	-162.55	
3.3	0.80	-173.57	4.88	-140.44	0.013	-168.44	0.63	-165.84	
3.4	0.84	-168.71	4.15	-150.46	0.012	-150.59	0.60	-169.06	
3.5	0.87	-163.87	3.53	-159.41	0.011	-141.43	0.60	-172.02	
3.6	0.90	-160.09	3.06	-166.50	0.011	-131.05	0.59	-175.55	
3.7	0.91	-156.40	2.64	-173.16	0.012	-125.73	0.59	-179.11	
3.8	0.92	-153.14	2.30	-179.41	0.011	-113.42	0.59	-176.78	
3.9	0.93	-149.64	1.98	-174.06	0.011	-101.43	0.59	-171.94	
4.0	0.94	-146.92	1.77	-167.95	0.010	-90.35	0.60	-167.39	
4.1	0.94	-144.72	1.56	-163.26	0.011	-90.76	0.60	-162.40	
4.2	0.95	-140.77	1.38	-157.72	0.012	-78.47	0.61	-157.76	
4.3	0.94	-138.91	1.22	-152.90	0.010	-79.13	0.62	-152.89	
4.4	0.94	-136.45	1.09	-146.89	0.010	-70.08	0.62	-147.89	
4.5	0.95	-133.43	0.98	-142.20	0.012	-59.32	0.64	-142.15	



ESD characteristic

Test Methodology	Class
Human Body Model (per JESD22-A114)	1C
Machine Model (per JESD22-A115)	A
Charged-Device Model (per JESD22-C101)	C3

Ordering Information

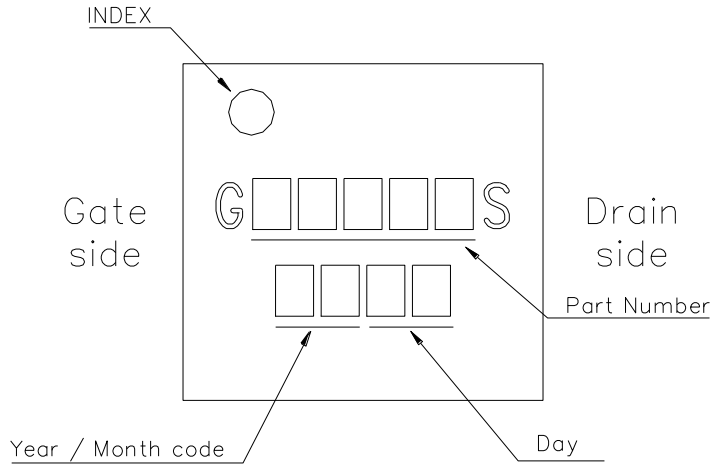
Part Number	MOQ	MOU	Packing Style
SGFCF15S-DT	2500pcs.	2500pcs.	Tape and Reel (16mm width Tape)
SGFCF15S-DT1	500pcs.	500pcs.	Tape and Reel (16mm width Tape)
SGFCF15S-D	20pcs.	20pcs.	Tray (4-inch)

Note : *MOQ stands for Minimum Order Quantity.
*MOU stands for Minimum Order Unit size.

Moisture Sensitivity Level

Level	Floor Life	
	Time	Condition
2a	4weeks after open the package	≤30deg.C/60%RH

Package Markings



Year code

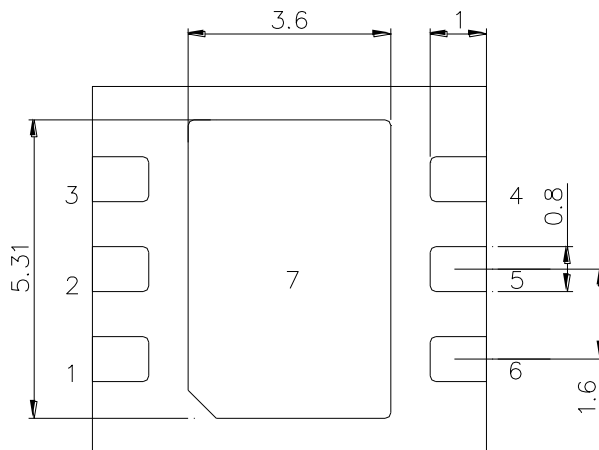
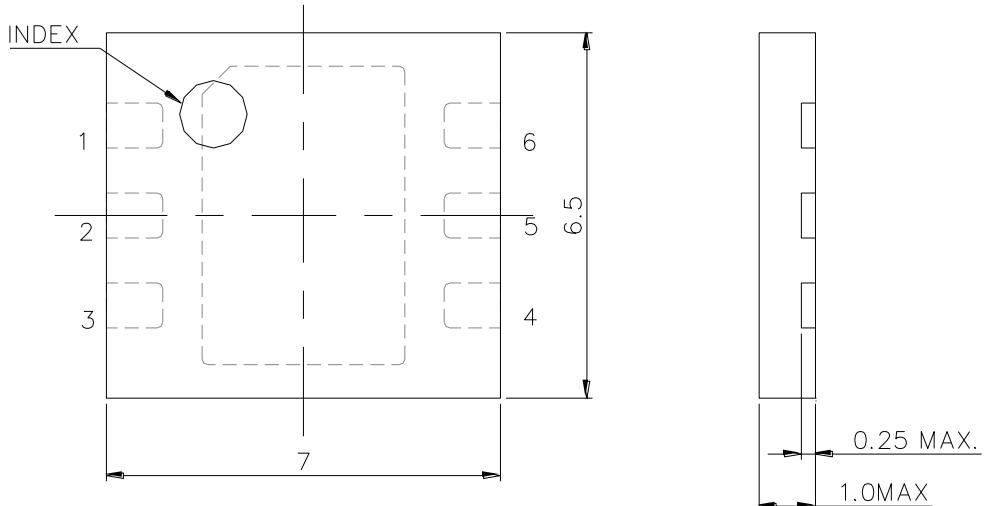
Year	2015	2016	2017	2018	2019	2020	2021	2022	2023
Code	X	Y	Z	A	B	C	D	E	F

Note: Code letter is cycling 25 alphabet without Q.

Month code

Month	Jan.	Feb.	Mar.	Apr.	May	Jun.	Jul.	Aug.	Sep.	Oct.	Nov.	Dec.
Code	H	M	N	P	R	S	T	U	W	X	Y	Z

Z2D Package Outline
Full Mold Plastic Package

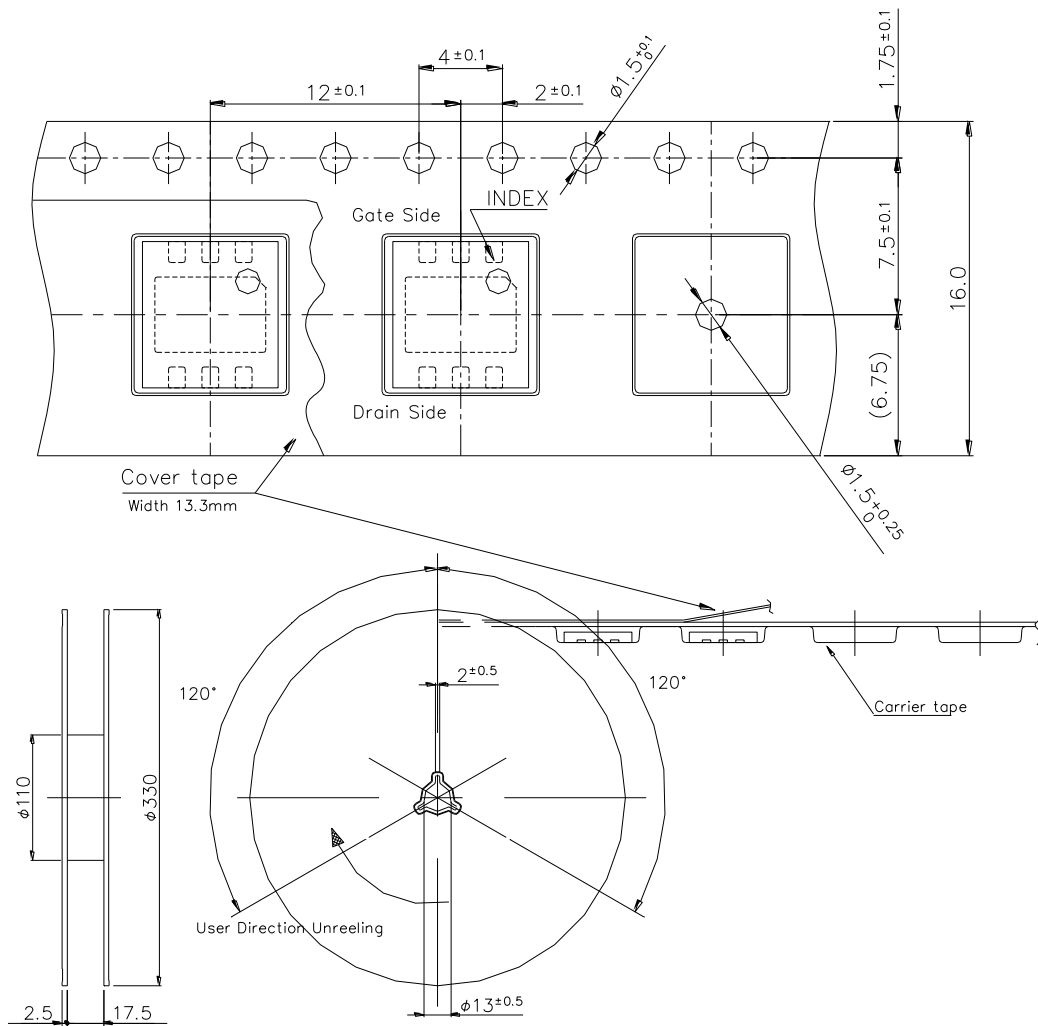


<Single Type>

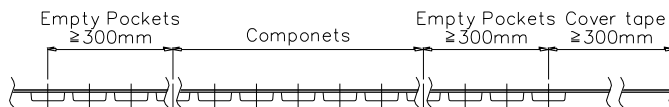
- 1 : NC
- 2 : Gate
- 3 : NC
- 4 : NC
- 5 : Drain
- 6 : NC
- 7 : Source

Unit: mm
 Tolerance : ±0.15mm

Index and Tape / Reel Configuration
 (Part Number : SGFCF15S-DT, SGFCF15S-DT1)



(Unit in mm)



- Note : Baking of Tape & Reel is possible by following condition.
1. Recommended Baking Condition : 125deg.C, 8hours
 2. Upper limit number of times : 5 times

* Reference standard : JIS standard(JIS C 0806-3)